

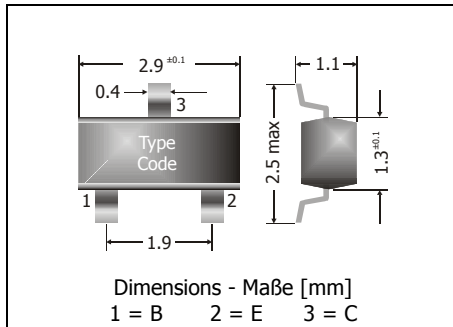
BC846 ... BC850

NPN

Surface Mount General Purpose Si-Epi-Planar Transistors
Si-Epi-Planar Universaltransistoren für die Oberflächenmontage

NPN

Version 2012-01-02



Power dissipation – Verlustleistung

250 mW

Plastic case
KunststoffgehäuseSOT-23
(TO-236)

Weight approx. – Gewicht ca.

0.01 g

Plastic material has UL classification 94V-0
Gehäusematerial UL94V-0 klassifiziertStandard packaging taped and reeled
Standard Lieferform getupet auf Rolle
Maximum ratings (T_A = 25°C)
Grenzwerte (T_A = 25°C)

			BC846	BC847	BC850	BC848 BC849
Collector-Emitter-volt. – Kollektor-Emitter-Spannung	B open	V _{CEO}	65 V	45 V	45 V	30 V
Collector-Base-voltage – Kollektor-Basis-Spannung	E open	V _{CBO}	80 V	50 V	50 V	30 V
Emitter-Base-voltage – Emitter-Basis-Spannung	C open	V _{EBO}	6 V		5 V	
Power dissipation – Verlustleistung		P _{tot}	250 mW ¹⁾			
Collector current – Kollektorstrom (dc)		I _C	100 mA			
Peak Collector current – Kollektor-Spitzenstrom		I _{CM}	200 mA			
Junction temperature – Sperrschichttemperatur		T _j	-55...+150°C			
Storage temperature – Lagerungstemperatur		T _s	-55...+150°C			

Characteristics (T_j = 25°C)
Kennwerte (T_j = 25°C)

			Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis V _{CE} = 5 V, I _C = 10 μA	Group A	h _{FE}	–	90	–
	Group B	h _{FE}	–	150	–
	Group C	h _{FE}	–	270	–
V _{CE} = 5 V, I _C = 2 mA	Group A	h _{FE}	110	180	220
	Group B	h _{FE}	200	290	450
	Group C	h _{FE}	420	520	800
Collector-Emitter saturation voltage – Kollektor-Sättigungsspannung ²⁾					
I _C = 10 mA, I _B = 0.5 mA I _C = 100 mA, I _B = 5 mA	V _{CEsat}		–	90 mV	250 mV
	V _{CEsat}		–	200 mV	600 mV
Base-Emitter saturation voltage – Basis-Sättigungsspannung ²⁾					
I _C = 10 mA, I _B = 0.5 mA I _C = 100 mA, I _B = 5 mA	V _{BEsat}		–	700 mV	–
	V _{BEsat}		–	900 mV	–

1 Mounted on P.C. board with 3 mm² copper pad at each terminal
 Montage auf Leiterplatte mit 3 mm² Kupferbelag (Löt-pad) an jedem Anschluss

2 Tested with pulses t_p = 300 μs, duty cycle ≤ 2% – Gemessen mit Impulsen t_p = 300 μs, Schaltverhältnis ≤ 2%

Characteristics (T_j = 25°C)
Kennwerte (T_j = 25°C)

		Min.	Typ.	Max.
Base-Emitter-voltage – Basis-Emitter-Spannung ²⁾				
V _{CE} = 5 V, I _C = 2 mA	V _{BE}	580 mV	660 mV	700 mV
V _{CE} = 5 V, I _C = 10 mA	V _{BE}	–	–	720 mV
Collector-Base cutoff current – Kollektor-Basis-Reststrom				
V _{CB} = 30 V, (E open)	I _{CBO}	–	–	15 nA
V _{CE} = 30 V, T _j = 125°C, (E open)	I _{CBO}	–	–	5 µA
Emitter-Base cutoff current				
V _{EB} = 5 V, (C open)	I _{EBO}	–	–	100 nA
Gain-Bandwidth Product – Transitfrequenz				
V _{CE} = 5 V, I _C = 10 mA, f = 100 MHz	f _T	–	300 MHz	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität				
V _{CB} = 10 V, I _E = i _e = 0, f = 1 MHz	C _{CBO}	–	3.5 pF	6 pF
Emitter-Base Capacitance – Emitter-Basis-Kapazität				
V _{EB} = 0.5 V, I _C = i _c = 0, f = 1 MHz	C _{EBO}	–	9 pF	–
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft		R _{thA}	< 420 K/W ¹⁾	
Recommended complementary PNP transistors Empfohlene komplementäre PNP-Transistoren		BC856 ... BC860		
Marking of available current gain groups Stempelung der lieferbaren Stromverstärkungsgruppen		BC846A = 1A BC846B = 1B	BC847A = 1E BC847B = 1F BC847C = 1G BC850B = 1F BC850C = 1G	BC848A = 1E BC848B = 1F BC848C = 1G BC849B = 1F BC849C = 1G

²⁾ Tested with pulses t_p = 300 µs, duty cycle ≤ 2% – Gemessen mit Impulsen t_p = 300 µs, Schaltverhältnis ≤ 2%

¹⁾ Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Löt-pad) an jedem Anschluss